

Innovative Laser Systems

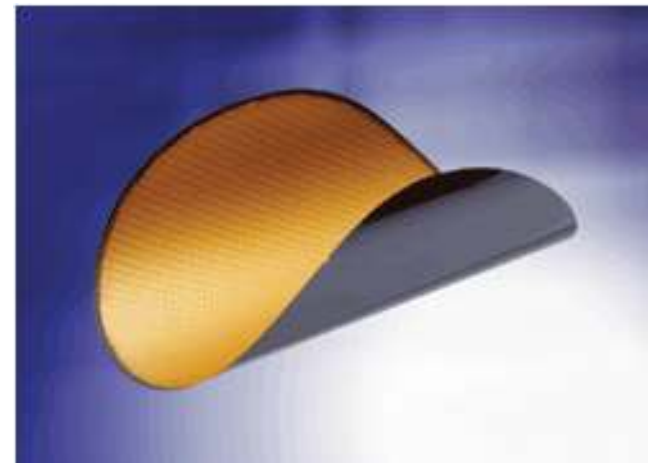
Semiconductors Power Devices



Synova Confidential

Agenda

- Synova History
- Laser MicroJet Technology (LMJ®)
- Market and Technology Overview
- Applications done by Synova
- Thin Wafer Processes
 - Taiko Ring, Temporary Bonding
- Solutions and Benefits



Partnering for the future

- Holland Private Equity (HPE) has invested 20M CHF in October 2011 for a minority stake in Synova S.A.
- Solid multiyear foundation in place:
 - To strengthen our Supply Chain and partner with Strategic Suppliers
 - Increase our Global Infrastructure for Sales and Support
 - Add Micro Machining Centers in South Korea, the USA and China
 - Invest in Strategic Developments to exceed our Customer's actual requirements and future expectations
 - Strengthen our core competencies



History

- Synova S.A. has shipped over 100 Systems since 1997 across the World
- Our Innovative Laser Systems and unique technology has been recognized by several awards



“Miles away from conventional laser”



“Going where no other laser can go”



“Water jet guided laser performs miracles”



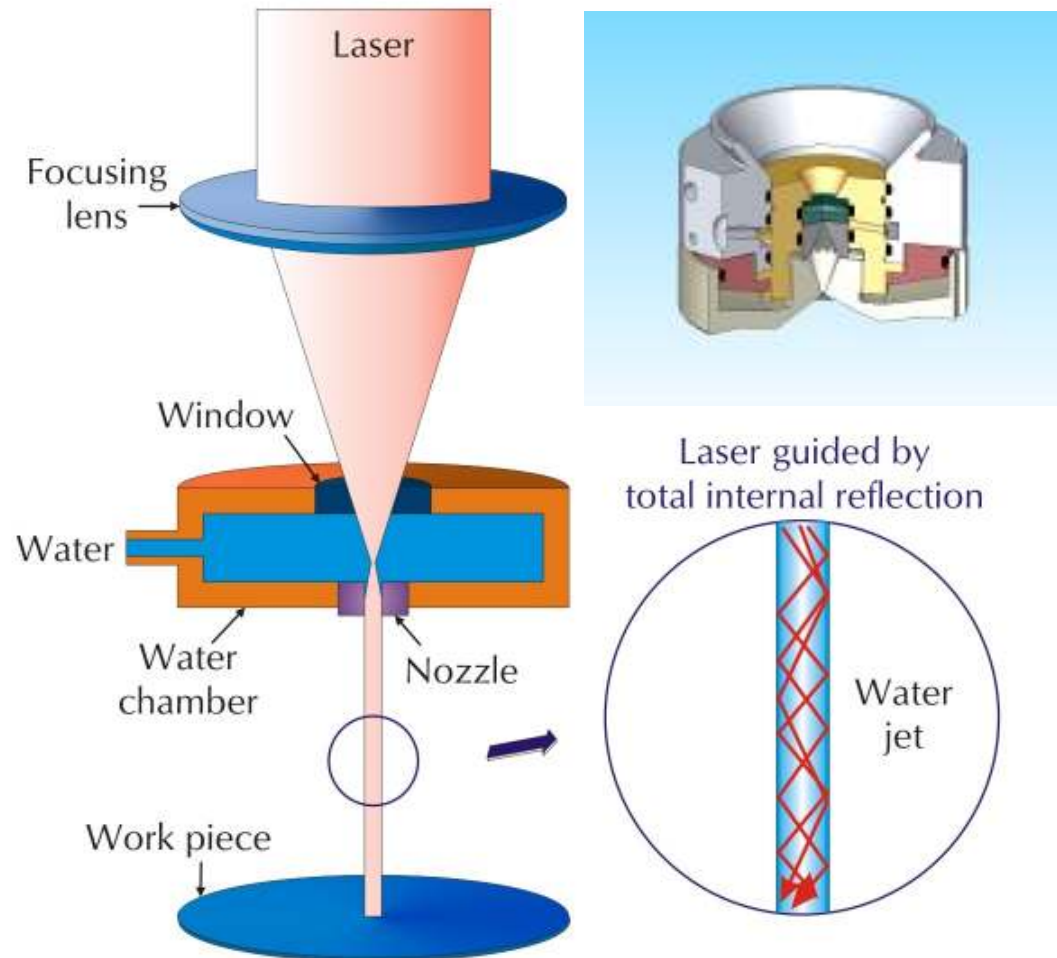
Global Infrastructure

Synova Worldwide










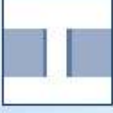
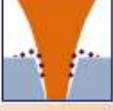
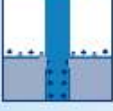

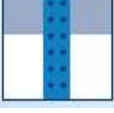
Laser Microjet Technology - a simple principle

- **A Revolution in Micromachining**
- For the first time ever, it is possible to combine the advantages of both water and laser cutting in one operation. Utilizing the difference in the refractive indices of air and water, the technology behind Laser MicroJet® creates a laser beam that is completely reflected at the air-water interface.
- The laser is, therefore, entirely contained within the water jet as a parallel beam, similar in principle to an optical fiber.



Technology advantages

The LMJ solves all drawbacks of conventional lasers

	Conventional Laser	Laser MicroJet®
	Requires precise focus adjustment 	No focus adjustment required, non-flat surfaces are not an issue, 3D cutting possible, variable cutting depth of up to several cm 
	Conical laser beam leaves non-parallel kerf walls 	Cylindrical beam results in parallel kerf walls, consistent high quality cutting 
Limitations in cutting aspect ratio		High aspect ratio, very small kerf widths (< 30 µm possible), minimising material loss, with simultaneous deep cuts possible 
Heat affected zone		Water-cooling process avoids thermal damage and material change, high fracture strength is maintained 
Particle deposition		A thin water film eliminates particle deposition and contamination, no surface protection layer required 
Inefficient material removal leaves burrs		The high kinetic energy of the water jet expels molten material, no burrs form 

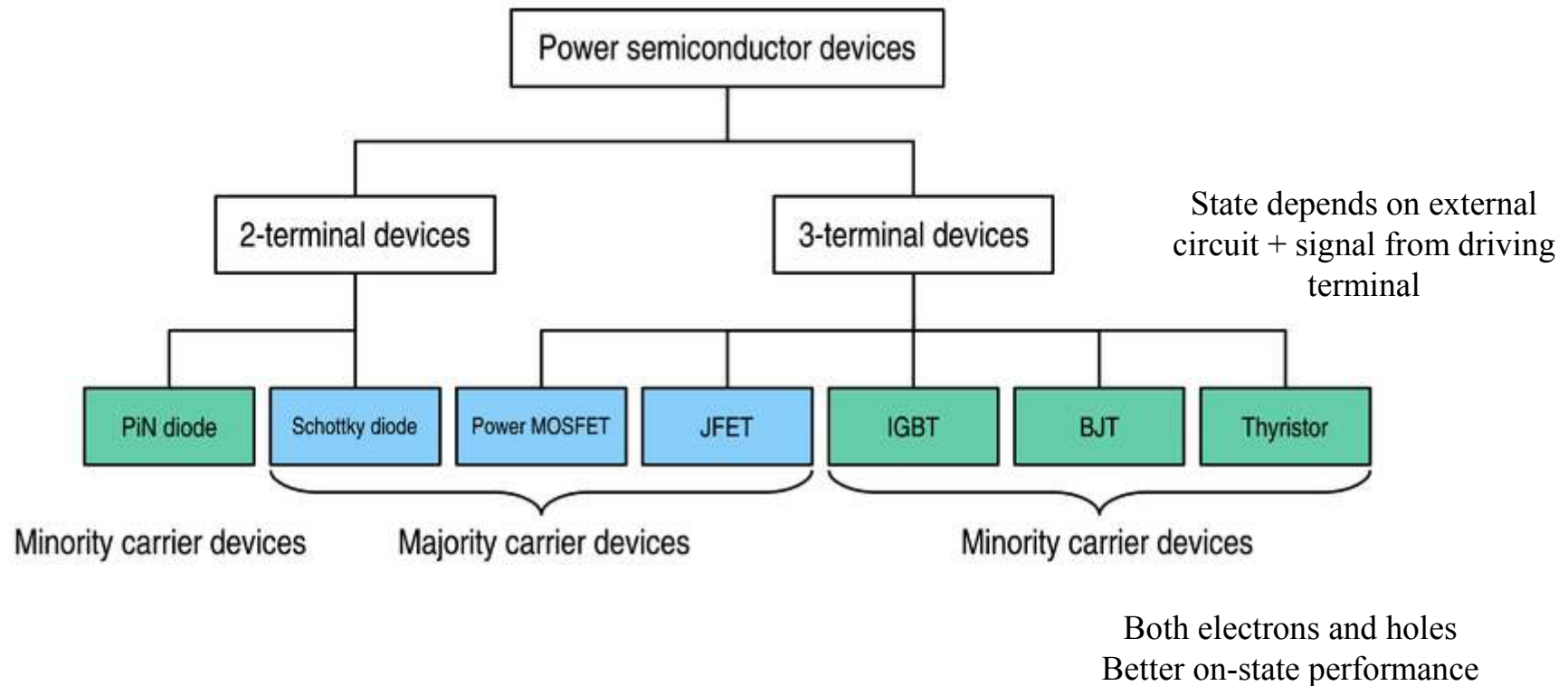


Power Semiconductors...Market Overview

- Technology Overview and Drivers
- Market Research

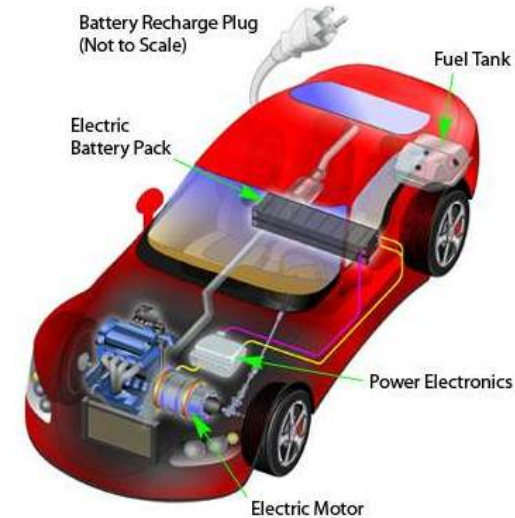


Power Semiconductor Classification

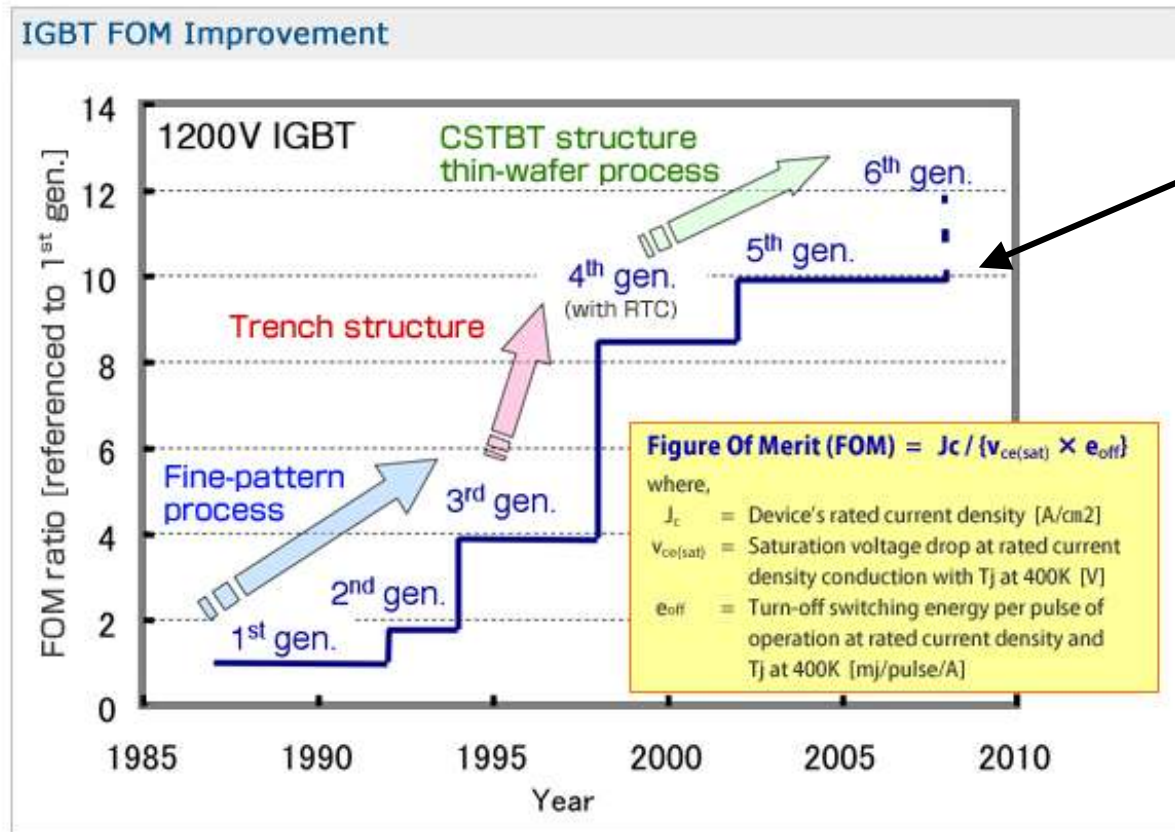


Major Drivers

- Traction
- Renewable energy
- Hybrid & Electric Vehicles
- High-power industrial drives
- Induction Heating and welding
- Consumer applications – Chinese Market
 - Appliances
 - Air Conditioning



IGBT Evolution



Need n-Field Stop Technology With Thinner Wafers

FOM shows that performance improved approximately fourfold between the 1st and 3rd-generation chips. And if the performance of the 1st-generation chip is compared with that of the current 5th-generation chip, it has improved approximately tenfold. As we proceed with the development of the 6th-generation device, our aim is to achieve not only even lower power loss, but also an improvement in performance indicators of approximately 30% as compared to the 5th-generation chip.

From Mitsubishi



SiC and GaN for future applications

Main applications accessible to SiC and GaN Specs / market data of today silicon devices

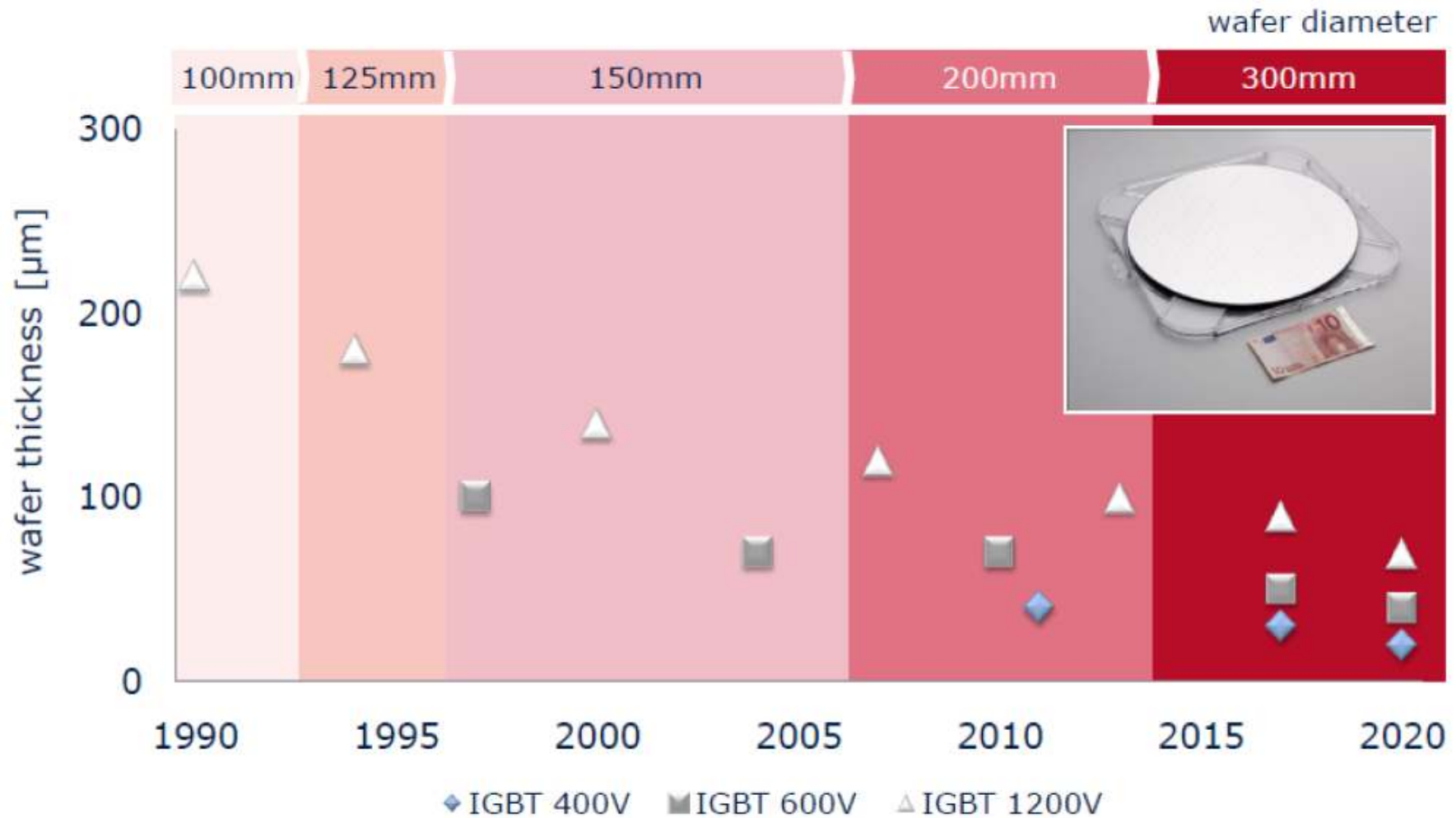


	Power supplies / PFC	UPS	HEV	Solar panel	Wind turbine	Industry Motor Drives	Energy Transport. Grid, Rail traction
Main devices	MOSFET Diodes	MOSFET IGBT Diodes	MOSFET IGBT Diodes	IGBT Diodes	IGBT Diodes	IGBT Diodes	GTO, Thyristor, IGBT PiN diode
Breakdown Voltage (V)	600 V	600 / 1200 V	650 V -> 900 V -> 1.2kV	600 V (90%) 1200 V (10%)	Today 690 V Trend: 3-4 kV	600 V to 1200 V	> 5 kV
Peak current (A) (for a single chip)	0.5 – 10 A	2 – 100 A	50 - 200 A	75 A	150 A	3 – 100 A	10 – 200 A
2008 volume (Munits)	MOS: 1,600 Diode: 1,600	IGBT: 800 Diode: 800	IGBT: 2.6 Diode: 2.6	IGBT: 12 Diode: 12	IGBT: 0.11 Diode: 0.11	IGBT: 25 Diode: 25	Wide range of specs / price
2008 ASP for a discrete device	Trans: \$0.6 - \$1 Diode: \$0.3	Trans: \$1.2 Diode: \$0.6	Trans: \$9 Diode: \$5	IGBT: \$8 Diode: \$4	IGBT: \$20 Diode: \$8	IGBT: \$8 Diode: \$4	
2008 Si devices market (\$M) (Discrete)	1,800	1,400	~ 40	150	< 3	~ 300	~ 110

Total Available Market was \$3.8B in 08



Infineon – Wafer Thickness Roadmap



Wafer Thinning

- Established process
 - Thinning through Grinding. Well established for Flash Memory
- Drivers for Power Devices
 - Improved Performance...better battery life
 - Improved Heat Dissipation
- Challenges
 - Additional handling with new post-grinding processes
 - Thickness down to 120 microns
 - Die strength greatly reduced
 - Substantial mechanical problems
 - Breakage
 - Microcracks
 - Reduced Fractural Strength

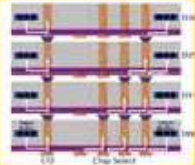


Drives the need for new laser-based edge removal and dicing

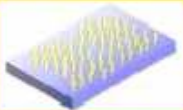


Thin Wafer Applications


Advanced packaging



3D stacking



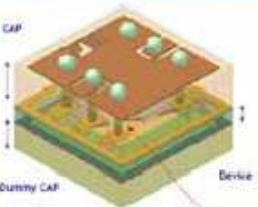
Interposer



Fan-Out WLP

Baseband+Tx+GPS

MEMS





CAP

Dummy CAP


Device

Cu Via




Source: SAIT

Compound semiconductor (LEDs, RF ...)



LEDs/HBLEDs



RF devices
GaAs, InP, SiC

Power devices (e.g. IGBTs)

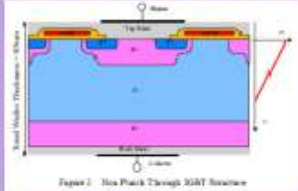

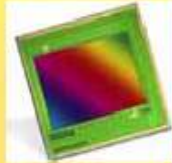
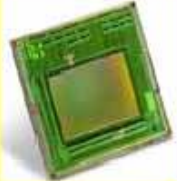


Figure 1: Non-Pack Through IGBT Structure

CMOS image sensors (Packaging, BSI)

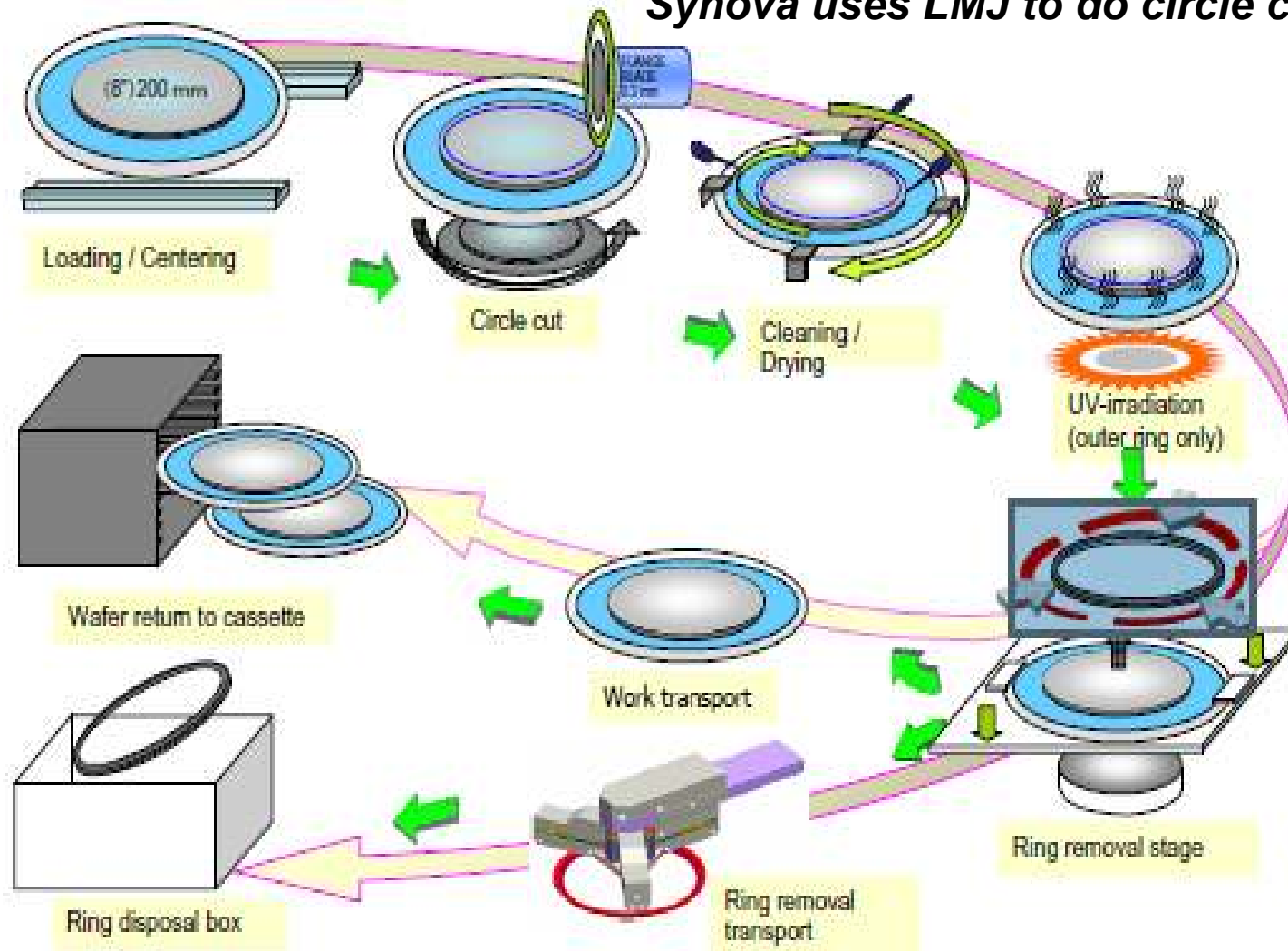


Taiko Wafer



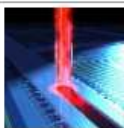


Taiko Ring Process Edge Grinding and Dicing

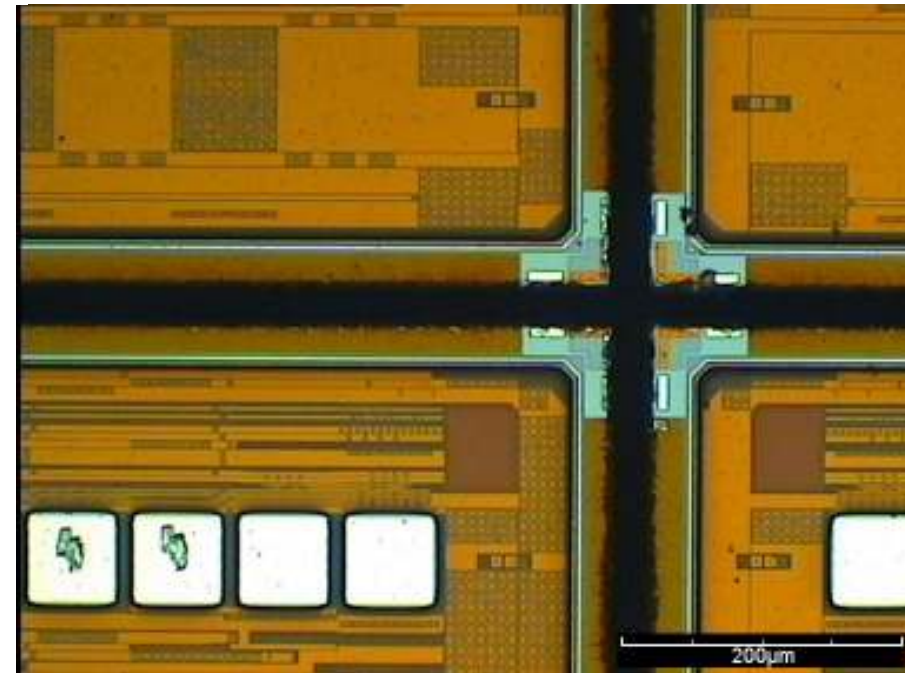
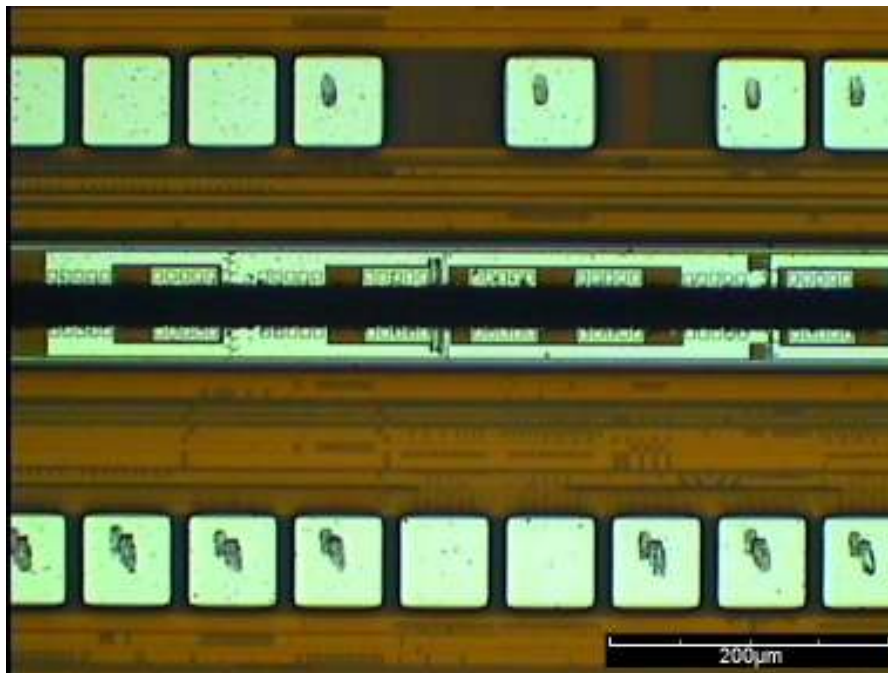
Synova uses LMJ to do circle cut and dicing



Thin Silicon Wafer Dicing

	MICROJET® PARAMETER	Nozzle diameter	30 μm
		MicroJet® diameter	27 μm
		Water pressure	450 bar
		Assist gas	He
	LASER PARAMETER	Laser type	L101G
		Wavelength	532 nm
		Pulse frequency	40 kHz
		Average power	18 W
	CUTTING PARAMETER	Cutting speed	200 mm/s
		Number of passes	8
		Overall speed	25 mm/s
		Tape	Lintec ADWILL 611

SAMPLE	Material	Silicon wafers
	Dimension	\varnothing 200 mm
	Thickness	150 μm



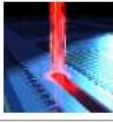


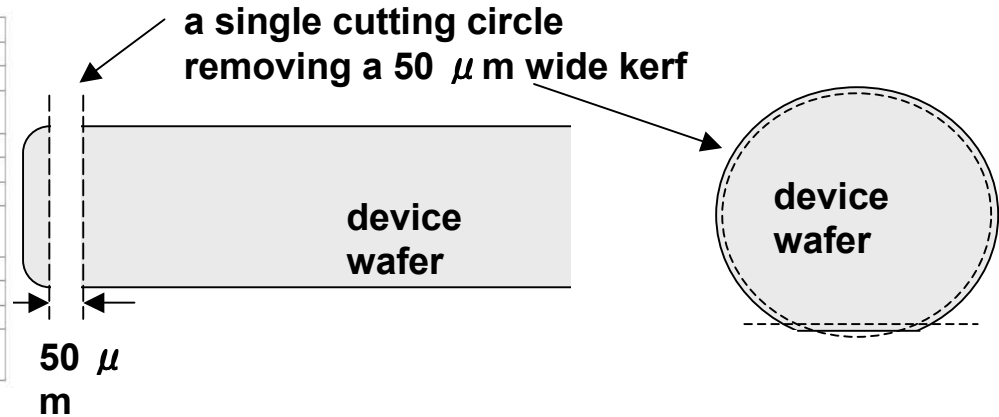
LMJ advantage vs saw: Less chipping, higher fracture strength, higher speed



Wafer Edge Grinding

SAMPLE	Material	Silicon wafers
	Dimension	Ø 150 / 200 mm
	Thickness	600 µm

	MICROJET® PARAMETER	Nozzle diameter	50 µm
		MicroJet® diameter	45 µm
		Water pressure	250 bar
		Assist gas	He
	LASER PARAMETER	Laser type	L101G
		Wavelength	532 nm
		Pulse frequency	23 kHz
		Average power	33 W
	CUTTING PARAMETER	Cutting speed	100 mm/s
		Number of passes	10
		Overall speed	10 mm/s



Wafer fracture strength improving before back grinding
 → yield improvement



Edge Grinding for Disco Taiko Wafer

The supporting edge ring can be cut off by the LMJ





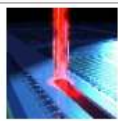
Before edge-grinding:



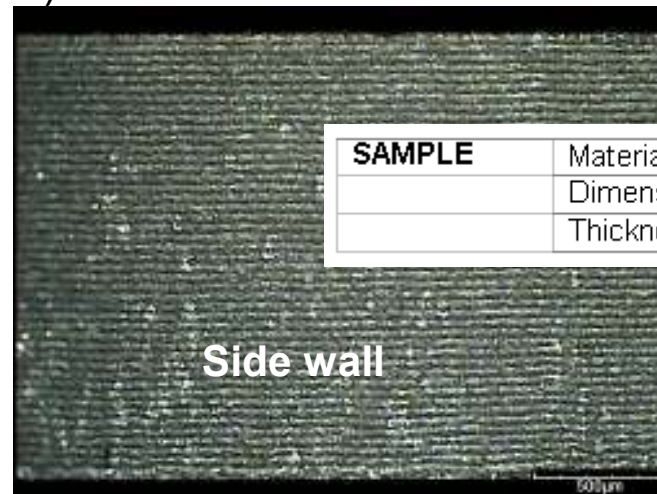
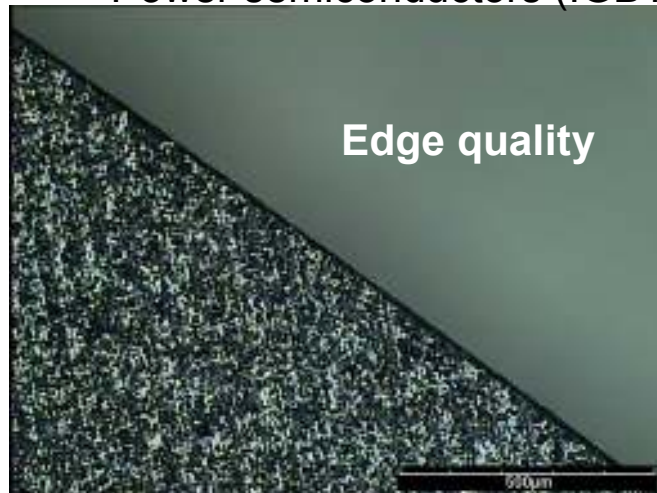
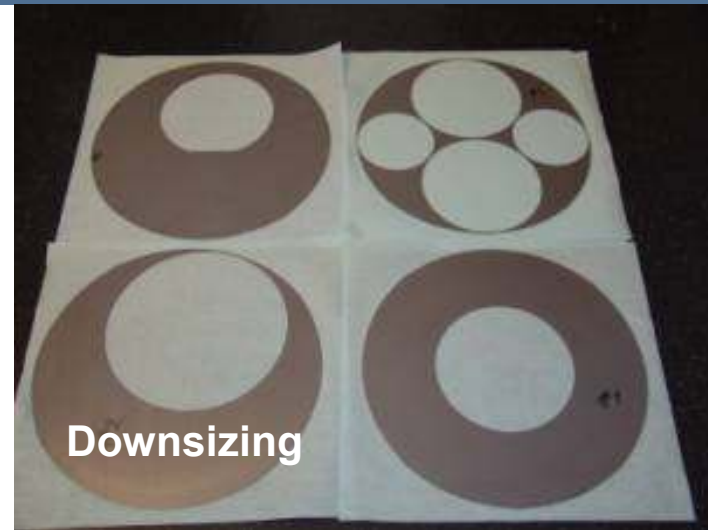
After edge-grinding:



Downsizing

	MICROJET® PARAMETER	Nozzle diameter	50 μm
		MicroJet® diameter	45 μm
		Water pressure	350 <i>bar</i>
		Assist gas	He
	LASER PARAMETER	Laser type	L101G
		Wavelength	532 <i>nm</i>
		Pulse frequency	15 <i>kHz</i>
		Average power	33 <i>W</i>
	CUTTING PARAMETER	Cutting speed	120 <i>mm/s</i>
		Ablation per passes	75 μm

- Very successful application for
 - Wafer downsizing
 - Power semiconductors (IGBT, GTO)



SAMPLE	Material	Silicon wafers	
	Dimension	Ø 100 - 300	<i>mm</i>
	Thickness	300 - 2500	μm

LMJ advantage vs. mechanical grinding: much better edge quality, much less chipping & cracks; any shape possible (incl. flat or notch)



Temporary Bonding Processes

		Bonding process/ Carrier	Equipment
Brewer Science (BSI)		Thermal bonding Si/Glass	<ul style="list-style-type: none"> • Spin coater • Bake plate • Aligner • Temporary bonder • Thinning systems • Inspection systems
TMAT		Thermal bonding Si/Glass	
3M WSS		UV light Glass	
Dupont		Thermal bonding Glass	
BSI: ZoneBond		Thermal bonding Si/Glass	
TOK		Thermal bonding Glass	

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YOLE DEVELOPEMENT



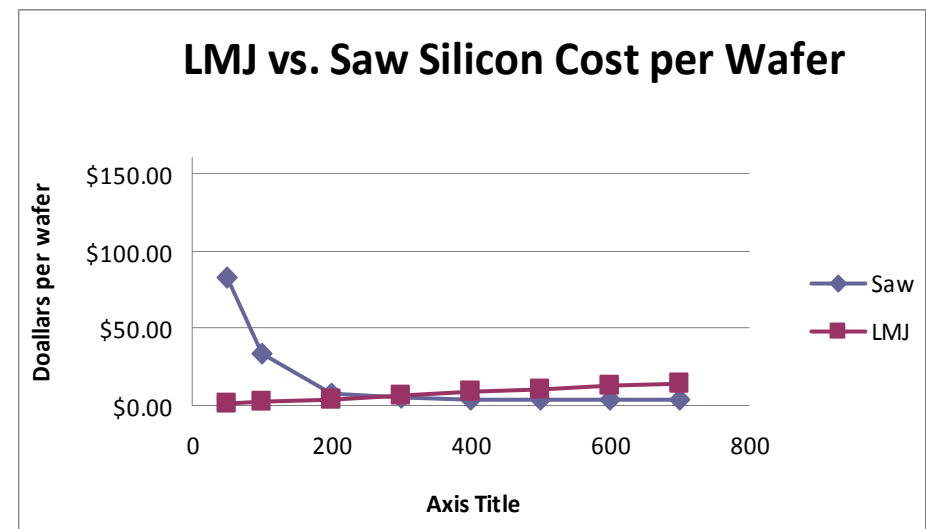
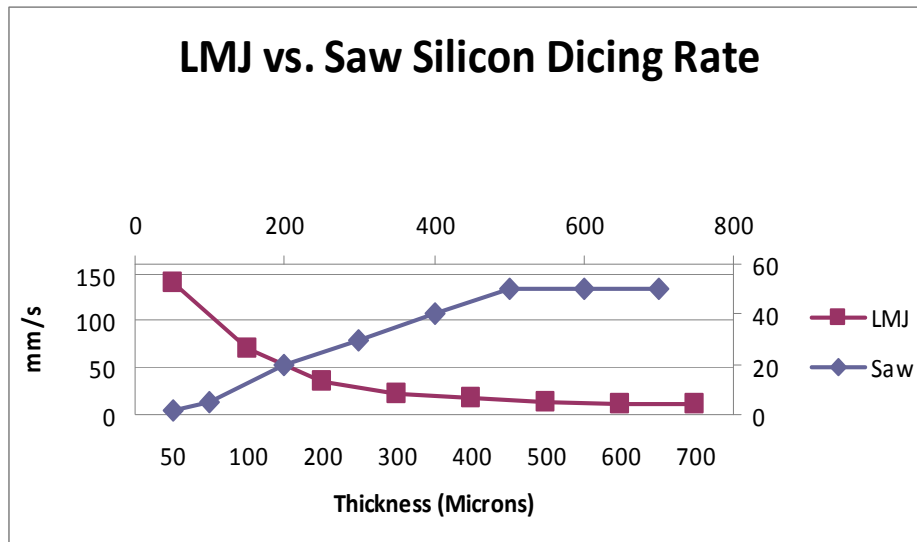
Advantages – Thin Silicon Wafers

	SAW	Laser	LMJ
Cost of Ownership	✗	✓	✓
Speed	✗	✓	✓
Edge quality	✗	✗	✓
Tool wear	✗	✓	✓
HAZ	✓	✗	✓
Flexibility	✗	✓	✓
Kerf width	✗	~	✓
Wide range of materials (SiC, GaN)	✗	✓	✓

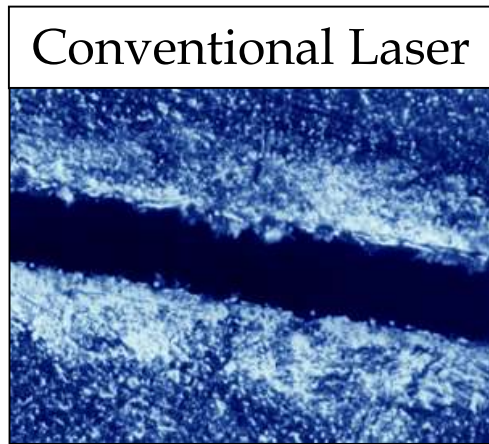


Benefits for Thin Wafers

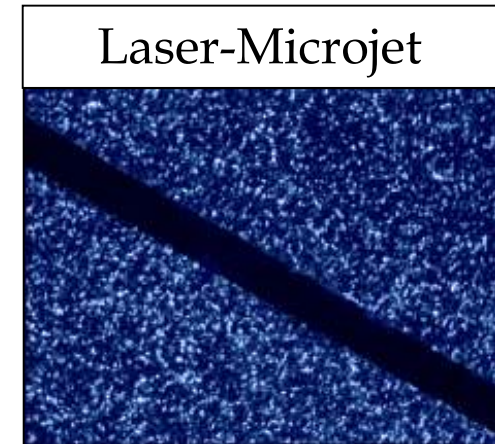
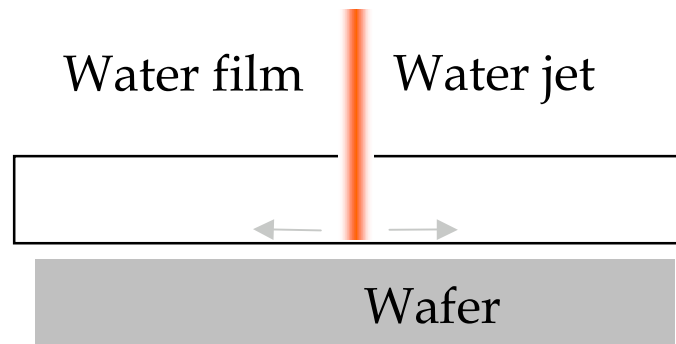
- Mechanical Saws need to slow down dramatically for Thin Wafers. Tool costs also increase. They cannot do Wafers with Flat Notches.
- Dry Lasers need larger Kerfs because of the Heat Affected Zones
- It is possible to do Edge Cutting and Dicing on same machine



Clean and No Thermal Damage Laser Cutting



As cut - need of protection



As cut - no need of protection

Enables to get clean post cut surface
Ensures Higher Break Strength



Summary for thinner Wafers

- The Laser Microjet technology improves the quality of the cut:
 - Less Mechanical and Thermal stresses than the Mechanical saw or the Dry laser
- Synova is also cost effective:
 - Saws need to slow down dramatically for thinner wafers and requires more consumable costs
 - Dry lasers are equivalent in terms of speed but they have a lower yield and wider kerf due to thermal stresses
- Synova has done both Edge Cutting for raw wafers and Taiko type Wafers as well as dicing

